

OXFORD INSTRUMENTS, RIE NGP80



- Wide range of materials can be etched (Si, SiO₂, Si₃N₄, glass, III-V, polymers)
- 240mm Electrode Size – can accommodate samples from 1 – 6 in
- Wafer stage temperature range: 10-80°C
- Single RF plasma source determines both ion density and energy
- 5-500 mTorr operating pressure